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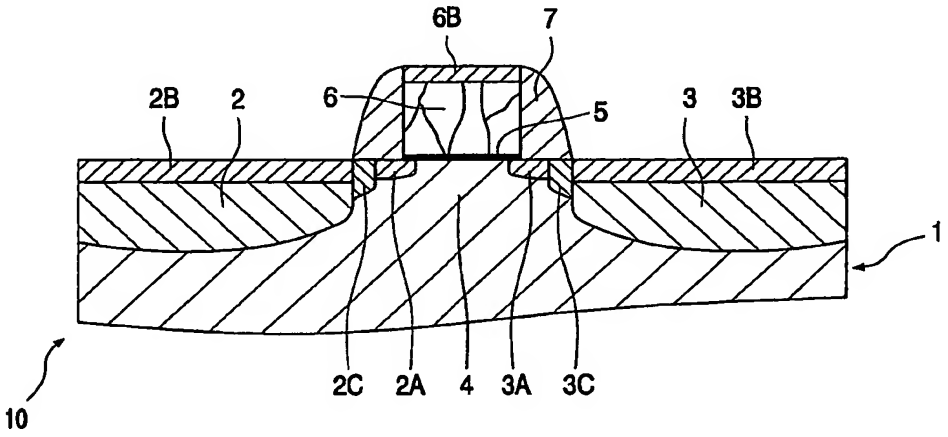
(54) Title: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING SUCH A SEMICONDUCTOR DEVICE



(57) Abstract: The invention relates to a semiconductor device (10) with a substrate and a semiconductor body (1) comprising a first FET (3) with a source (2) and a drain (3) that are provided with connection regions (2B, 3B) of a metal silicide, and that are connected to source and drain extensions (2A, 3A) bordering a channel region (4) below a gate (6) and having a smaller thickness and a lower doping concentration than the source (2) and the drain (3). The source (2) and drain (3) and the source and drain extensions (2A, 3A) are connected to each other by means of an intermediate region (2C, 3C) of the first conductivity type having a thickness and a doping concentration ranging between the thickness and doping concentration of the source (2) and drain (3) and the extensions (2A, 3A) thereof. In this way, the occurrence of leakage currents and the risk of a short-circuit between the connection regions (2B, 3B) and the substrate is limited, while the advantages of the use of source and drain extensions (2A, 3A) are preserved. Preferably, the intermediate regions (2C, 3C) are positioned below spacers (7) next to the gate (6), and they are preferably formed using a, preferably tilted, ion implantation.

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